SEMICONDUCTOR

SS810B

SCHOTTKY BARRIER RECTIFIER

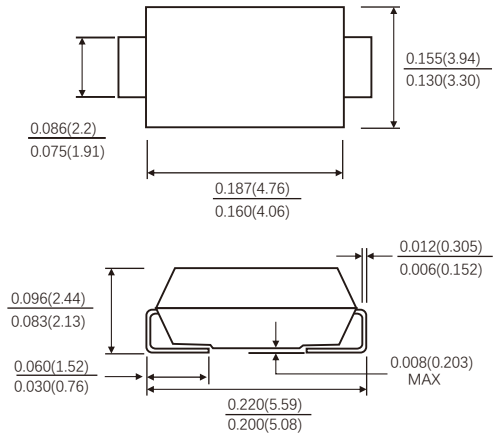
Reverse Voltage-100Volts
Forward Current-8.0Amperes

FEATURES

- Plastic package has Underwriters Laboratory Flammability Classification 94V-0
- Metal silicon junction ,majority carrier conduction
- Guard ring for overvoltage protection
- Low power loss ,high efficiency
- High current capability ,low forward voltage drop
- High surge capability
- High temperature soldering guaranteed:260℃/10 seconds at terminals
- Component in accordance to RoHS 2015/863/EU

Pb RoHS COMPLIANT

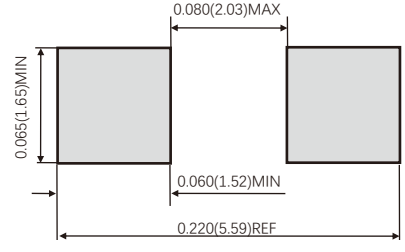
SMB(DO-214AA)



MECHANICAL DATA

- Case: JEDEC SMB(DO-214AA) molded plastic body
- Terminals: Solder Plated, solderable per MIL-STD-750,method 2026
- Polarity: Color band denotes cathode end
- Weight: 0.003ounce, 0.093 gram

Suggested PAD Layout



Dimensions in inches and (millimetrers)

TYPICAL APPLICATIONS

For use in low voltage,high frequency inverter,DC/DC converters, free wheeling,and polarity protection applications

MAXIMUM RATINGS

(Ratings at 25℃ ambient temperature unless otherwise)

Parameter	Symbol	Value	Unit
Maximum repetitive peak reverse voltage	V_{RRM}	100	V
Maximum average forward rectified current	$I_{F(AV)}$	8.0	A
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC method at rated TL)	I_{FSM}	150	A
Operating junction temperature range	T_J	-55 to +150	℃
Storage temperature range	T_{stg}	-55 to +150	℃

ELECTRICAL CHARACTERISTCS（T_A=25℃ Unless otherwise noted）

Parameter	Test Conditions		Symbol	Typ.	Max.	Unit
Instaneous Forward Voltage	T_A=25℃	I_F=1A	V_F 1)	0.50	-	V
		I_F=3A		0.62	-	
		I_F=8A		0.75	0.82	
	T_A=125℃	I_F=1A		0.40		
		I_F=3A		0.51	-	
		I_F=8A		0.63	-	
Reverse Current	T_A=25℃	V_R=100V	I_R 2)	-	5	μA
	T_A=125℃			-	5.0	mA
Typical Junction Capacitance	4V,1MHz		C_J	260		pF

Notes: 1.Pulse test: 300 μs pulse width,1% duty cycle

2.Pulse test: pulse width≤40ms

THERMAL CHARACTERISTCS

Parameter	Symbol	SMB	Unit
Typical thermal resistance 3)	$R_{\theta JA}$	70.0	℃/W
	$R_{\theta JL}$	15.0	

3. Unit mounted on PC board with 5.0mm×5.0 mm (0.013 mm thick) copper pads as heat sink, (dPtot/dtj) < ($1/R_{\theta JA}$) is thermal runaway condition for a diode

AVAILABALE PACK INFORMATION

Product code	Pack	Reel Size (mm)	Quantity (pcs/reel)	Box Size L×W×H (mm)	Quantity (reel/box)	Carton Size L×W×H (mm)	Quantity (box/carton)	Quantity (K/carton)
SS810B-SMB	T/R	Φ330	3000	330×333×39	2	370×370×360	8	48

RATINGS AND CHARACTERISTICS OF SS810B

Fig.1-Forward Current Derating Curve

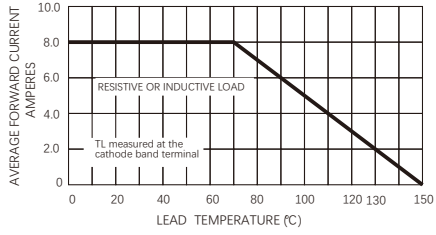


Fig.2-maximum Non-repetitive Peak Forward Surge Current

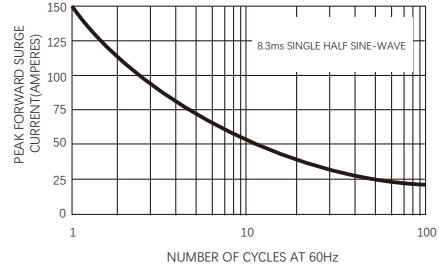


Fig.3-Typical Instantaneous Forward Characteristics

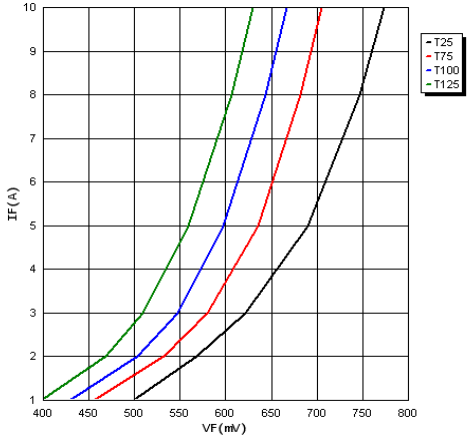


Fig.4-Typical Reverse Characteristics

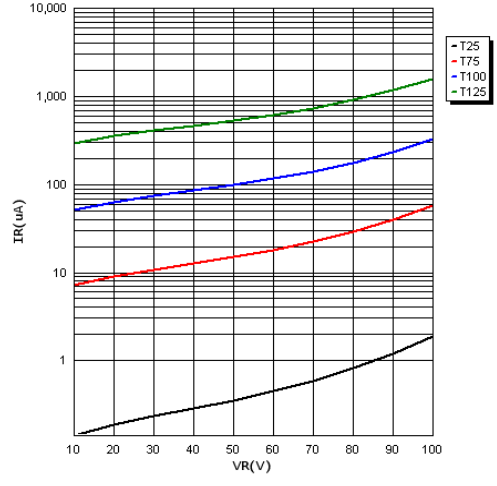
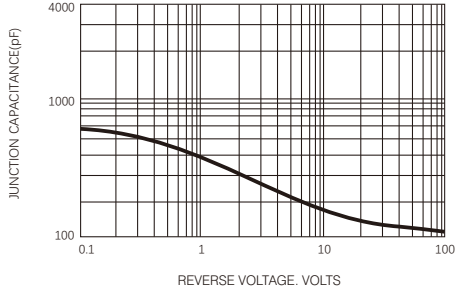


Fig.5-Typical Junction Capacitance



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